

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination HONG ET AL.	
		Examiner Steven H. Rao	Art Unit 2814	Page 1 of 1

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	B	US-6,376,911	04-2002	Ryan et al.	257/752
	C	US-6,762,126	07-2004	Cho et al.	438/694
	D	US-6,869,860	03-2005	Belyansky et al.	438/435
	E	US-6,878,463	04-2005	Skrobis, Amy V.	428/630
	F	US-6,204,161	03-2001	Chung et al.	438/612
	G	US-6,706,646	03-2004	Lee et al.	438/782
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	U	Jung-Ho Lee et al., " A study of ILD Process of simple amd CMP Skip using Polysilazane-based SOG, IEEE, 2001, 317-320.
	V	Jung-Sik Choi et al., " A Shallow Trench Isolation using Novel Polysilizane-based SOG for Deep-Submicron Technologies and Beyond" IEEE 2003, 419-422
	W	Tsubaki Junichiro, " Development of ceramic Nano-porous Materials" 2002, 167- 170.
	X	Tsali Cross et al. " Fabrication Process for Ultra High Aspect ratio Polysilazane- Derived MEMS " IEEE, 2002, 172-175.

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.